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Supporting information for article:

Multiple Epitaxial Lateral Overgrowth of GaN Thin Films Using a Patterned Graphene Mask by Metal Organic Chemical Vapor Deposition

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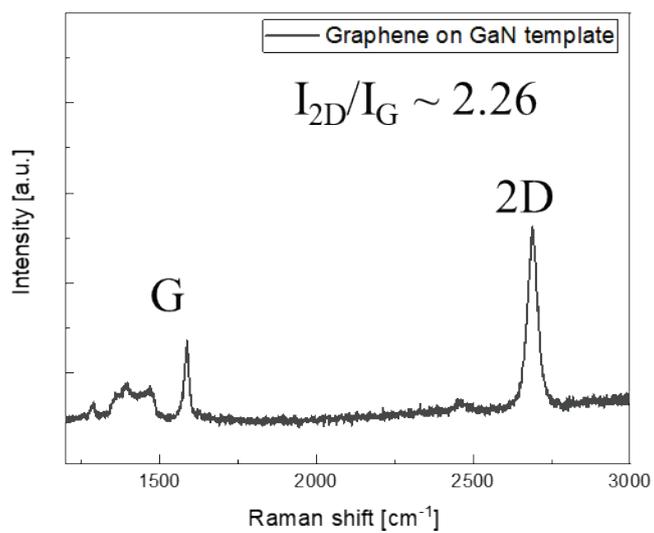


Fig. S1. Raman spectra of transferred graphene on GaN template. The intensity ratio of 2D/G (I_{2D}/I_G) was 2.26. Single-layer graphene can be distinguished from multi-layer graphene which has a broad 2D band and low intensity of 2D/G of under 1

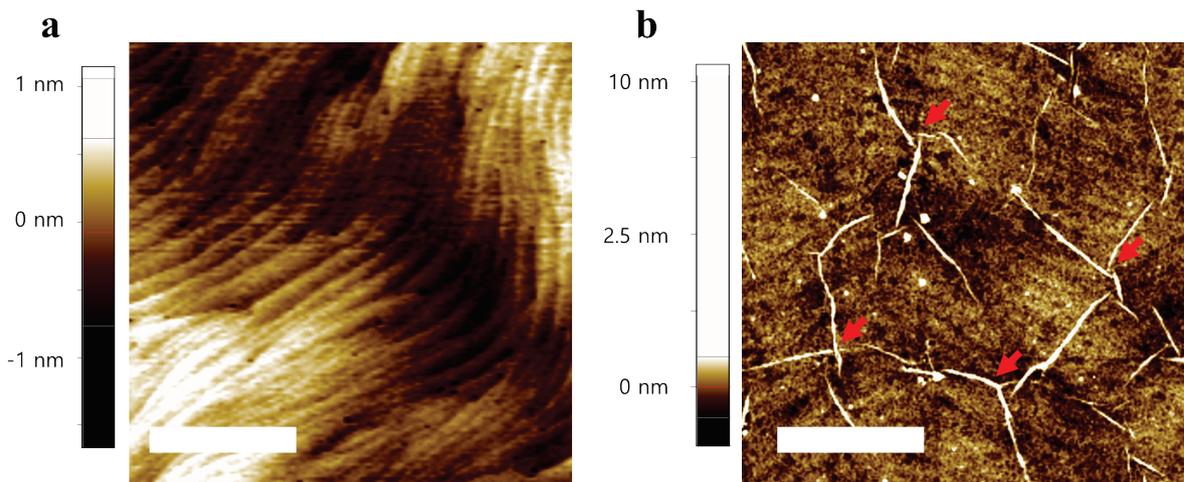


Fig. S2. Atomic force microscopy images of (a) a bare GaN template and (b) a transferred graphene on a GaN template. The measured root-mean-square (RMS) roughness value of the GaN template and the transferred graphene were 0.354 nm and 0.507 nm. Considering the RMS roughness value of the GaN template and the local wrinkle of graphene (red arrows), the graphene was transferred relatively flat on GaN template. In addition, trace of the terrace of the GaN template was observed after graphene transfer.